

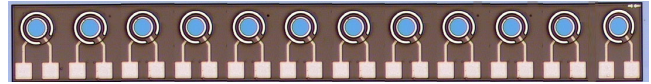
Features

- : Two top-side wire bond pads per channel
- : AR coated for 850nm
- : Low dark current and low capacitance
- : Uniform characteristics
- : Data rate 2.5 / 3.125Gbps per Channel
- : Other configurations available on request

Applications

- : High speed Data Communications
- : Gigabit Ethernet
- : Fiber Channel

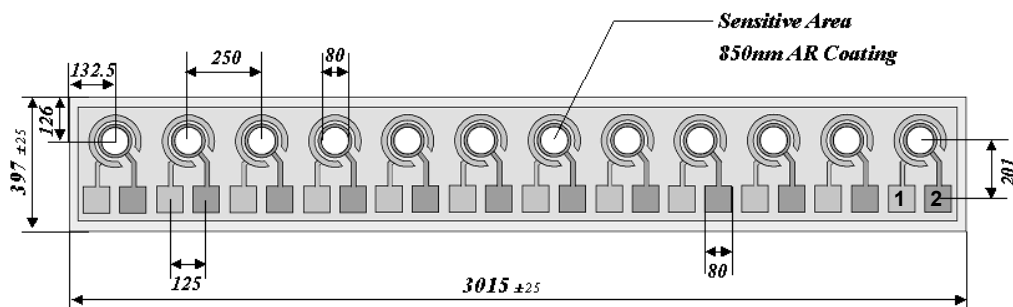
Description



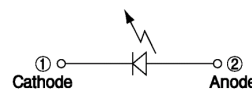
Absolute Maximum Ratings

Parameter	Rating
Forward Current	10mA
Reverse Voltage	40V
Operating Temperature	0 to 85 °C
Storage Temperature	-40 to 100 °C

Dimensions



Unit: μm
Height: 200±15 μm



Electro-Optics Characteristics (T_a=25°C unless otherwise stated)

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Sensitive Area	D		80		μm	In diameter
Responsivity	R	0.5	0.6		A/W	V _R = 1.6V, λ =850nm
Dark Current	I _D		0.1	1.0	nA	V _R = 1.6V
Breakdown Voltage	V _B	40			V	I _R = 1 μA
Capacitance	C		0.4	0.5	pF	V _R = 1.6V, f=1MHz
Peak Wavelength	λ		850		nm	
Rise and Fall times	t _r /t _f		100/100		ps	V _R =1.6V, 20% ~ 80%
Bandwidth	f _{-3dB}		5.0		GHz	V _R =1.6V

Notes

- Substrate : Semi-insulating GaAs.
- Specific active area, pad size and shapes can be provided on customer's request.

* These specifications are subject to change without notice.

NOTICE

The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product

Characteristics Curves

